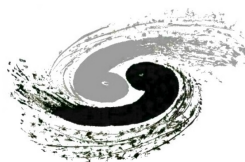
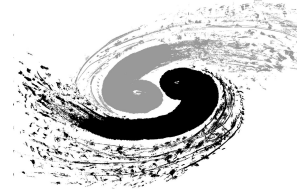


Sensor Design Update

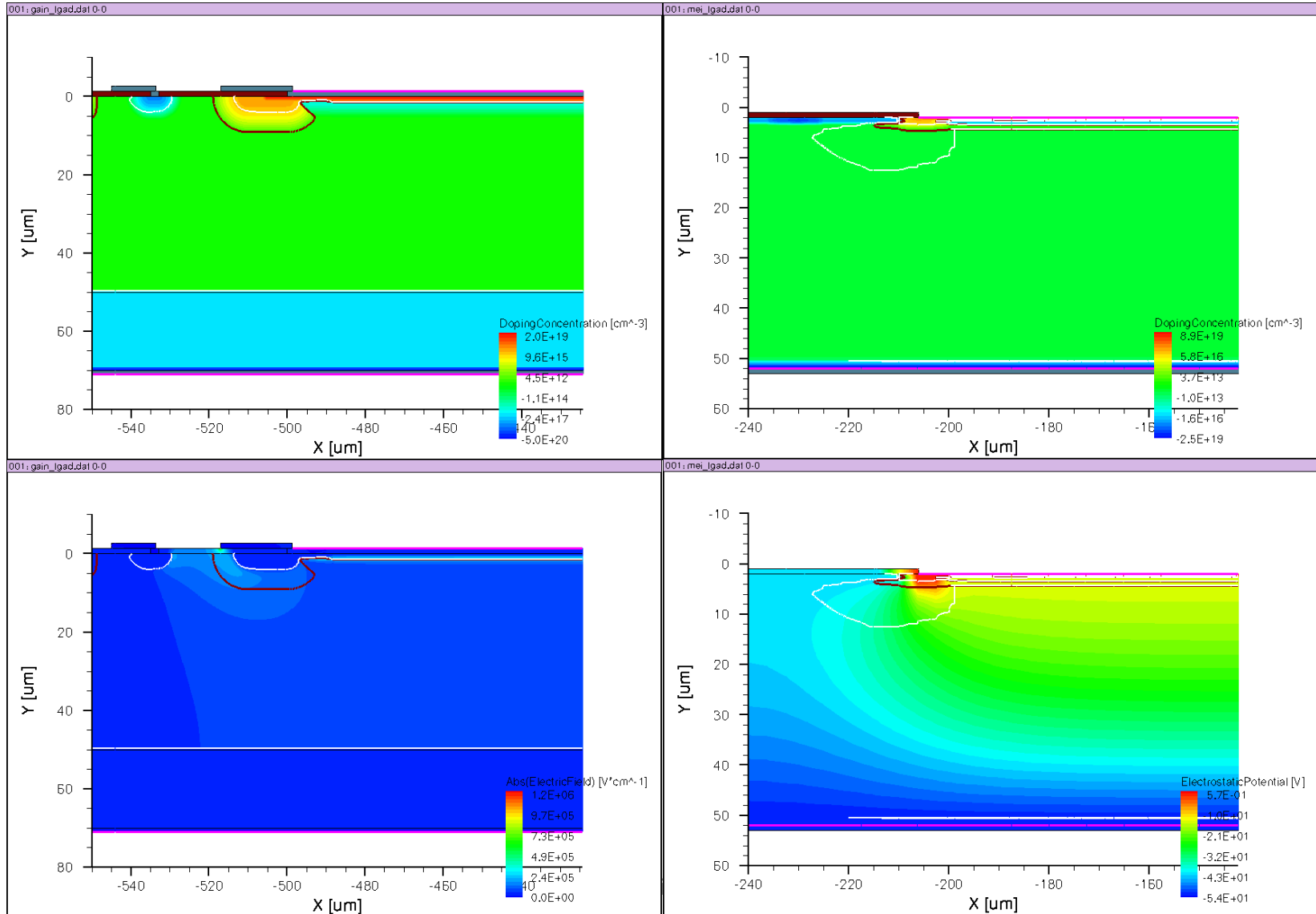


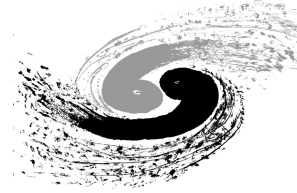
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2019/04/11



Process Simulation





P Layer Implantation

Does/ 10^{12}cm^{-2}	Ennegy/keV	Breakdown Voltage/V
1	100	160
5	100	15
10	100	12
15	100	10
20	100	6.5
5	80	30
5	120	14

Summary

1. Make sure crystal orientation(1 0 0).
2. Discuss Boron Ion Injection times (once or twice).
3. Use lower dose($<2 \times 10^{12} \text{cm}^{-2}$) according to results.
4. Need energy maximum(especially N-JTE energy).

Thanks for your listening!



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